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Sheet 1 of 2

Form 1449*	Atty. Docket No.: 303.684US2	Serial No. <u>Unknown</u>
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes	10/042924
	Filing Date: Herewith 01/09/02	Group: <u>Unknown</u> 2813

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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
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Examiner <u>William Alegria</u>	Date Considered <u>7-11-2003</u>
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*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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W. H. Lee

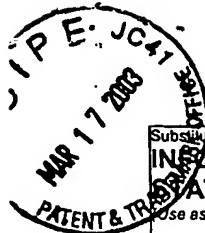
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Substitute for form 1449A/PTO
**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Use as many sheets as necessary)

<i>Complete if Known</i>	
Application Number	10/042924
Filing Date	January 9, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2822 2813
Examiner Name	Unknown VESPERMAN

Sheet 1 of 1

Attorney Docket No: 303.684US2

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Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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